M O Manasreh

List of Publications by Year
in descending order

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115 papers	2,145 citations	257450 24 h-index	265206 42 g-index
115 all docs	115 docs citations	115 times ranked	1558 citing authors

#	Article	IF	Citations
1	Solution Processed High Efficiency Quantum Dot Light Emitting Diode With Inorganic Charge Transport Layers. IEEE Electron Device Letters, 2018, 39, 536-539.	3.9	12
2	Vertically grown zinc oxide nanorods functionalized with ferric oxide forinvivoand non-enzymatic glucose detection. Nanotechnology, 2018, 29, 115501.	2.6	24
3	An In-Vitro Optical Sensor Designed to Estimate Glycated Hemoglobin Levels. Sensors, 2018, 18, 1084.	3.8	22
4	Sensitivity enhancement in an in-vitro glucose sensor using gold nanoelectrode ensembles. Journal of Materials Science: Materials in Electronics, 2017, 28, 5452-5459.	2.2	10
5	Investigation of charge transport between nickel oxide nanoparticles and CdSe/ZnS alloyed nanocrystals. MRS Advances, 2017, 2, 2935-2941.	0.9	1
6	All inorganic quantum dot light emitting devices with solution processed metal oxide transport layers. MRS Advances, 2016, 1, 305-310.	0.9	8
7	The impact of quantum dot filling on dual-band optical transitions via intermediate quantum states. Journal of Applied Physics, 2015, 118, 084501.	2.5	1
8	Self-Powered Near-Infrared Photodetector Based on Asymmetrical Schottky Interdigital Contacts. IEEE Electron Device Letters, 2015, 36, 1172-1175.	3.9	22
9	Near-infrared metal-semiconductor-metal photodetector based on semi-insulating GaAs and interdigital electrodes. Photonics Research, 2015, 3, 1.	7.0	22
10	Uncooled photodetectors based on CdSe nanocrystals with an interdigital metallization. Applied Physics Letters, 2014, 104, 051124.	3.3	12
11	Enhanced response in InAs quantum dots in an InGaAs quantum well solar cells by anti-reflection coatings. Materials Research Society Symposia Proceedings, 2013, 1551, 155-161.	0.1	0
12	Influence of template type and buffer strain on structural properties of GaN multilayer quantum wells grown by PAMBE, an x-ray study. Journal Physics D: Applied Physics, 2011, 44, 025403.	2.8	12
13	Multicolor photodetector based on GaAs quantum rings grown by droplet epitaxy. Applied Physics Letters, 2009, 94, .	3.3	76
14	Intermediate-band material based on GaAs quantum rings for solar cells. Applied Physics Letters, 2009, 95, .	3.3	57
15	Growth of nonpolar cubic GaN/AlN multiple quantum wells with intersubband transitions for 1.5 Âµm applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2092-2095.	0.8	0
16	Polarized Raman spectroscopy and X-ray diffuse scattering in InGaAs/GaAs(100) quantum-dot chains. Journal of Materials Science: Materials in Electronics, 2008, 19, 692-698.	2.2	4
17	Room Temperature Near-Infrared Photoresponse Based on Interband Transitions in $hbox{In}_{0.35}hbox{Ga}_{0.65}hbox{As}$ Multiple Quantum Dot Photodetector. IEEE Electron Device Letters, 2008, 29, 224-227.	3.9	25
18	Cubic GaNâˆ•AlN multiple quantum well photodetector. Applied Physics Letters, 2008, 92, 201910.	3.3	25

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19	Dual broadband photodetector based on interband and intersubband transitions in InAs quantum dots embedded in graded InGaAs quantum wells. Applied Physics Letters, 2007, 91, .	3.3	31
20	Near-infrared intersubband absorption in nonpolar cubic GaNâˆ•AlN superlattices. Applied Physics Letters, 2007, 91, .	3.3	24
21	Proton Irradiation Effect on CdSe-ZnS Core-Shell Nanocrystals Embedded in Ultra Violet Curable Resin. , 2007, , .		1
22	Temperature dependence of the band gap of colloidal CdSeâˆ•ZnS core/shell nanocrystals embedded into an ultraviolet curable resin. Applied Physics Letters, 2006, 89, 131907.	3.3	80
23	Near-infrared wavelength intersubband transitions in GaNâˆ•AlN short period superlattices. Applied Physics Letters, 2006, 89, 151112.	3.3	12
24	Investigation of indium distribution in InGaAsâˆ•GaAs quantum dot stacks using high-resolution x-ray diffraction and Raman scattering. Journal of Applied Physics, 2006, 99, 023517.	2.5	26
25	Intersubband transitions in proton irradiated InGaAsâˆ•GaAs multiple quantum dots. Applied Physics Letters, 2005, 87, 091905.	3.3	3
26	Proton irradiation effect on single-wall carbon nanotubes in a poly(3-octylthiophene) matrix. Applied Physics Letters, 2005, 86, 221908.	3.3	13
27	Determination of the carrier concentration in InGaAsNâˆ•GaAs single quantum wells using Raman scattering. Applied Physics Letters, 2004, 85, 4905-4907.	3.3	8
28	Tuning In0.3Ga0.7Asâˆ•GaAs multiple quantum dots for long-wavelength infrared detectors. Applied Physics Letters, 2004, 85, 1003-1005.	3.3	17
29	Photoluminescence of metalorganic-chemical-vapor-deposition-grown GaInNAs/GaAs single quantum wells. Applied Physics Letters, 2003, 82, 514-516.	3.3	5
30	Infrared optical absorbance of intersubband transitions in GaN/AlGaN multiple quantum well structures. Journal of Applied Physics, 2003, 93, 10140-10142.	2.5	15
31	Optical absorption of intersubband transitions in In0.3Ga0.7As/GaAs multiple quantum dots. Applied Physics Letters, 2003, 82, 2509-2511.	3.3	8
32	Thermal annealing effect on nitrogen vacancy in proton-irradiated AlxGa1âˆ’xN. Applied Physics Letters, 2002, 80, 2072-2074.	3.3	12
33	Response to â€œComment on â€˜Thermal annealing effect on the intersublevel transitions in InAs quantum dotsâ€™â€Šâ€•[Appl. Phys. Lett. 80, 4867 (2002)]. Applied Physics Letters, 2002, 80, 4869-4870.	3.3	1
34	Structural disorder in ion-implanted AlxGa1âˆ’xN. Applied Physics Letters, 2002, 80, 787-789.	3.3	39
35	Intersubband transitions in proton irradiated In0.52Ga0.48As/In0.52Al0.48As multiple quantum wells grown on semi-insulating InP substrate. Applied Physics Letters, 2002, 81, 3374-3376.	3.3	7
36	Interband Transitions in GaInNAs/GaAs Single Quantum Wells. Materials Research Society Symposia Proceedings, 2002, 744, 1.	0.1	0

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37	Intersubband Transitions in Proton Irradiated InGaAs/InAlAs Multiple Quantum Wells Grown on Lattice Matched InP Substrate. Materials Research Society Symposia Proceedings, 2002, 744, 1.	0.1	0
38	Ion-beam-produced damage and its stability in AlN films. Journal of Applied Physics, 2002, 92, 3554-3558.	2.5	58
39	Observation of nitrogen vacancy in proton-irradiated AlxGa1â^'xN. Applied Physics Letters, 2001, 79, 2901-2903.	3.3	22
40	Thermal annealing effect on the intersublevel transitions in InAs quantum dots. Applied Physics Letters, 2001, 78, 2196-2198.	3.3	10
41	Intersubband Transitions In Ingaas/Inalas Multiple Quantum Wells Grown On Inp Substrate. Materials Research Society Symposia Proceedings, 2001, 692, 1.	0.1	0
42	Thermal Anneal Effects on Carbon-Hydrogen LVMs In AlGaN. Materials Research Society Symposia Proceedings, 2001, 692, 1.	0.1	0
43	Local Vibrational Modes of Carbon-Hydrogen Complexes in Proton Irradiated AlGaN. Materials Research Society Symposia Proceedings, 2001, 692, 1.	0.1	0
44	Optical Absorption of Nitrogen Vacancy in Proton Irradiated AlxGa1-xN thin Films. Materials Research Society Symposia Proceedings, 2001, 693, 50.	0.1	0
45	He+â€“ion irradiation effect on intersubband transitions in GaAs/AlGaAs multiple quantum wells. Journal of Applied Physics, 2001, 89, 3517-3519.	2.5	7
46	Localized Vibrational Modes of Carbon-Hydrogen Complexes in MOCVD Grown GaN and AlGaN thin films. Materials Research Society Symposia Proceedings, 2000, 639, 311.	0.1	0
47	Optical Absorption of Doped and Undoped Bulk SiC. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	1
48	Thermal annealing recovery of intersubband transitions in proton-irradiated GaAs/AlGaAs multiple quantum wells. Applied Physics Letters, 2000, 77, 2867-2869.	3.3	7
49	Degradation of Intersubband Transitions in Electron Irradiated GaAs/AlGaAs Multiple Quantum Wells With Superlattice Barriers. Materials Research Society Symposia Proceedings, 1999, 607, 503.	0.1	1
50	Localized vibrational modes of carbon-hydrogen complexes in GaN. Applied Physics Letters, 1999, 75, 659-661.	3.3	23
51	Electron irradiation effects on the intersubband transitions in InGaAs/AlGaAs multiple quantum wells. Journal of Applied Physics, 1999, 85, 630-632.	2.5	10
52	Proton irradiation effects on the intersubband transition in GaAs/AlGaAs multiple quantum wells with bulk or superlattice barriers. Applied Physics Letters, 1999, 75, 525-527.	3.3	12
53	Photoluminescence Measurements in Interband Transition in Fast Neutron Irradiated In0.07Ga0.93As/A10.4Ga0.6 As Multiple Quantum Wells. Materials Research Society Symposia Proceedings, 1999, 607, 525.	0.1	1
54	Thermal Annealing Recovery of Intersubband Transition in Proton-Irradiated GaAs/Al0.3Ga0.7As Multiple Quantum Wells. Materials Research Society Symposia Proceedings, 1999, 607, 217.	0.1	0

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55	Exchange interaction effect on the dark current in n-type AlxGa1â^'xAs/GaAs multiple quantum wells infrared detectors. Journal of Applied Physics, 1997, 81, 1305-1310.	2.5	6
56	Î³-Ray Irradiation Effect on the Intersubband Transition in Ingaas/Aigaas Multiple Quantum Wells. Materials Research Society Symposia Proceedings, 1997, 484, 637.	0.1	5
57	Optical absorption near the band edge in GaN grown by metalorganic chemical-vapor deposition. Physical Review B, 1996, 53, 16425-16428.	3.2	75
58	Theoretical Studies of Electronic Intersubband Transitions in n-Type Doped Quantum Wells for Infrared Photodetector Applications. Materials Research Society Symposia Proceedings, 1996, 450, 173.	0.1	0
59	Intersubband transitions in tripleâ€coupled quantum wells for threeâ€colors infrared detectors. Journal of Applied Physics, 1996, 80, 6045-6049.	2.5	15
60	Intersubband transitions in strainedIn0.07Ga0.93As/Al0.40Ga0.60As multiple quantum wells and their application to a two-colors photodetector. Physical Review B, 1996, 54, 5620-5628.	3.2	37
61	Reply to â€˜â€˜Comment on â€˜Many-body analysis of the effects of electron density and temperature on the intersubband transition in GaAs/AlxGa1â^'xAs multiple quantum wellsâ€™â€™â€™. Physical Review B, 1996, 54, 10980-10981.	3.2	0
62	Many-body analysis of the effects of electron density and temperature on the intersubband transition in GaAs/AlxGa1â^'xAs multiple quantum wells. Physical Review B, 1995, 52, 14126-14130.	3.2	30
63	Additional H-related local vibrational modes in proton-implanted InP. Semiconductor Science and Technology, 1994, 9, 1-4.	2.0	19
64	Temperature dependence of the direct band gap energy and donorâ€“acceptor transition energies in Beâ€doped GaAsSb lattice matched to InP. Applied Physics Letters, 1994, 65, 2442-2444.	3.3	23
65	Theory for the oscillatory cyclotron resonance effective mass in a heterostructure. Journal of Applied Physics, 1994, 75, 902-907.	2.5	2
66	Temperature and many-body effects on the intersubband transition in a GaAs/Al0.3Ga0.7As multiple quantum well. Physical Review B, 1994, 50, 11618-11623.	3.2	21
67	Moving photoluminescence bands in GaAs1â^'xSbxlayers grown by molecular beam epitaxy on InP substrates. Journal of Applied Physics, 1994, 76, 504-508.	2.5	20
68	Intersubband Transitions in In0.07Ga0.93As/Al0.4Ga0.6As Multiple Quantum Wells. Materials Research Society Symposia Proceedings, 1994, 299, 53.	0.1	1
69	Optical absorption of the intersubband transitions in GaAs/Al0.4Ga0.6As multiple quantum wells with superlattice barriers. Journal of Applied Physics, 1993, 73, 3105-3107.	2.5	5
70	Electron paramagnetic resonance study of the twoâ€dimensional electron gas in Ga1â^'xAlxSb/InAs single quantum wells. Applied Physics Letters, 1993, 62, 90-92.	3.3	8
71	Isochronal annealing of local vibrational modes in protonâ€and deuteronâ€implanted InP. Journal of Applied Physics, 1993, 73, 78-83.	2.5	11
72	Hydrogenâ€iron interaction in protonâ€implanted InP:Fe. Applied Physics Letters, 1993, 63, 3038-3039.	3.3	3

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73	Electron-paramagnetic-resonance study of GaAs grown by low-temperature molecular-beam epitaxy. Physical Review B, 1992, 45, 3372-3375.	3.2	38
74	Local mode spectroscopy of protonâ€•and deuteronâ€•implanted InP. Journal of Applied Physics, 1992, 71, 4805-4808.	2.5	17
75	Incorporation of silicon and aluminum in low temperature molecular beam epitaxial GaAs. Applied Physics Letters, 1992, 60, 2377-2379.	3.3	6
76	Intersubband optical absorption in heavily dopedn-type GaAs/Al0.3Ga0.7As multiple quantum wells. Physical Review B, 1992, 46, 7208-7211.	3.2	14
77	Effect of Al Composition on the Deep Level Donors of AlxGa1-xSb/InAs Single Quantum Wells. Materials Research Society Symposia Proceedings, 1992, 262, 893.	0.1	0
78	Hydrogen Complexes and their Vibrations in Proton and Deuteron Implanted Inp: Theory and Experiment. Materials Research Society Symposia Proceedings, 1992, 291, 561.	0.1	0
79	Negative persistent photoconductivity in the Al0.6Ga0.4Sb/InAs quantum wells. Applied Physics Letters, 1992, 60, 751-753.	3.3	48
80	Intersubband Infrared Absorption in a GaAs/Al0.3Ga0.7As Multiple Quantum Well. NATO ASI Series Series B: Physics, 1992, , 287-297.	0.2	0
81	Spin-Splitting and Effective Mass of the 2-Dimensional Electron Gas in an Al0.6Ga0.4Sb/InAs Single Quantum Well. Materials Research Society Symposia Proceedings, 1991, 240, 765.	0.1	0
82	Incorporation of Silicon in Low Temperature Molecular Beam Epitaxial GaAs. Materials Research Society Symposia Proceedings, 1991, 241, 27.	0.1	0
83	Electron Paramagnetic Resonance Study of Low Temperature Molecular Beam Epitaxy Grown GaAs and InP Layers. Materials Research Society Symposia Proceedings, 1991, 241, 69.	0.1	2
84	Response to: â€˜â€˜Comment on â€˜The effect of charge state on the local vibrational mode absorption of the carbon acceptor in semiâ€•insulating GaAsâ€™â€‰â€™â€™. Journal of Applied Physics, 1991, 69, 6733-6734.	2.5	4
85	Origin of the blueshift in the intersubband infrared absorption in GaAs/Al0.3Ga0.7As multiple quantum wells. Physical Review B, 1991, 43, 9996-9999.	3.2	60
86	Anomalous behavior of cyclotron resonance in GaAs/Al0.28Ga0.72As high-electron-mobility transistor structures. Physical Review B, 1991, 43, 9772-9776.	3.2	19
87	Infrared absorption of deep defects in molecular-beam-epitaxial GaAs layers grown at 200 Â°C: Observation of anEL2-like defect. Physical Review B, 1990, 41, 10272-10275.	3.2	135
88	The effect of charge state on the local vibrational mode absorption of the carbon acceptor in semiâ€•insulating GaAs. Journal of Applied Physics, 1990, 68, 2504-2506.	2.5	13
89	Intersubband infrared absorption in a GaAs/Al0.3Ga0.7As quantum well structure. Applied Physics Letters, 1990, 57, 1790-1792.	3.3	53
90	Incorporation of carbon in heavily doped AlxGa1â^'xAs grown by metalorganic molecular beam epitaxy. Applied Physics Letters, 1990, 57, 294-296.	3.3	44

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91	Far-infrared absorption from shallow acceptors and its relationship to the persistent photocurrent in semi-insulating GaAs. Semiconductor Science and Technology, 1990, 5, 994-996.	2.0	6
92	Anomalous Hall-effect results in low-temperature molecular-beam-epitaxial GaAs: Hopping in a denseEL2-like band. Physical Review B, 1990, 42, 3578-3581.	3.2	273
93	Photoquenching and photoinduced-recovery properties of theEL2defect in GaAs: Evidence against the identification ofEL2with the isolatedAsGadefect. Physical Review B, 1989, 39, 13001-13004.	3.2	9
94	Electron-irradiation effects on the infrared absorption properties of theEL2 defect in GaAs. Physical Review B, 1989, 39, 3871-3874.	3.2	11
95	Noncreation of theEL2defect in neutron-irradiated GaAs. Physical Review B, 1989, 40, 5814-5816.	3.2	2
96	Temperature dependence of the photoinduced EL2*â†'EL20recovery process observed by infrared absorption. Applied Physics Letters, 1989, 54, 2018-2020.	3.3	18
97	Infrared absorption properties of theEL2 and the isolatedAsGadefects in neutron-transmutation-doped GaAs: Generation of anEL2-like defect. Physical Review B, 1989, 39, 3239-3249.	3.2	26
98	Observation of the second energy level of the EL2 defect in GaAs by the infrared absorption technique. Applied Physics Letters, 1989, 55, 864-866.	3.3	14
99	Quenching and recovery characteristics of theEL2 defect in GaAs under monochromatic-light illumination. Physical Review B, 1989, 40, 11756-11763.	3.2	24
100	Photoluminescence bands of deep centres in neutron-transmutation-doped GaAs. Semiconductor Science and Technology, 1989, 4, 435-438.	2.0	6
101	The EL2 Defect in GaAs: Some Recent Developments. Physica Status Solidi (B): Basic Research, 1989, 154, 11-41.	1.5	68
102	Optical Absorption of Deep Defects in Neutron Irradiated Semi-Insulating GaAs.. Materials Research Society Symposia Proceedings, 1989, 163, 175.	0.1	0
103	Recovery from the Metastable EL2 Defect in GaAs Under Monochromatic Light Illumination.. Materials Research Society Symposia Proceedings, 1989, 163, 827.	0.1	0
104	Ultrasonic attenuation peaks near the diffuse solid-electrolyte transition temperature inPbF2andBaF2. Physical Review B, 1988, 38, 6270-6273.	3.2	7
105	Infrared absorption of electron irradiation induced deep defects in semiâ€insulating GaAs. Applied Physics Letters, 1988, 53, 2429-2431.	3.3	23
106	Neutron irradiation effects on the infrared absorption of theEL2 defect in GaAs: New interpretation for the intracenter transition. Physical Review B, 1988, 37, 6567-6570.	3.2	15
107	Comment on â€˜â€˜Atomic model for theEL2defect in GaAsâ€™â€™. Physical Review B, 1988, 37, 2722-2723.	3.2	4
108	Optical Absorption of the Isolated AsGa Antisite and An EL2 - Like Defect in neutron-Transmutation Doped GaAs.. Materials Research Society Symposia Proceedings, 1988, 138, 273.	0.1	0

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109	New evidence of small lattice relaxation for theDXcenter in AlxGa1â^'xAs. Applied Physics Letters, 1987, 51, 1358-1360.	3.3	11
110	Fourier-transform infrared-absorption studies of intracenter transitions in theEL2level in semi-insulating bulk GaAs grown with the liquid-encapsulated Czochralski technique. Physical Review B, 1987, 35, 2524-2527.	3.2	19
111	Infrared-absorption properties ofEL2 in GaAs. Physical Review B, 1987, 36, 2730-2734.	3.2	12
112	Attenuation of transverse ultrasonic waves near the diffuse solid electrolyte transition inCdF2. Physical Review B, 1985, 31, 8153-8156.	3.2	8
113	Elastic constants of barium fluoride from 300 to 1250 K. Physical Review B, 1985, 31, 3960-3964.	3.2	21
114	Elastic constants of cubic lead fluoride from 300 to 850 K. Physical Review B, 1984, 30, 3482-3485.	3.2	38
115	Highâ€temperature acoustic bond compatible with fluoride fluorites. II. Transverse ultrasonic measurements in barium fluoride. Journal of the Acoustical Society of America, 1984, 75, 1766-1769.	1.1	9